## **Dual N-Channel 30-V (D-S) MOSFET**

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$I_{D}(A)$				
30	$35 @ V_{GS} = 10V$	6.4			
	$45 @ V_{GS} = 4.5V$	5.6			

- $\hbox{ Low $r_{DS(on)}$ provides higher efficiency and} \\ \hbox{ extends battery life}$
- Low thermal impedance copper leadframe DFN2x3 saves board space
- Fast switching speed
- High performance trench technology

	CF1206-8 Top View			D <sub>1</sub>	$D_2$
S1 G1 S2 G2	1 2 3 4	8 7 6 5	□ D <sub>1</sub> □ D <sub>1</sub> □ D <sub>2</sub> □ D <sub>2</sub>	G <sub>1</sub> S <sub>1</sub> N-Channel MOSFET	$\mathbf{G}_2 \circ \bigcup_{\mathbf{S}_2} \mathbf{S}_2$ N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Units			
Drain-Source Voltage	$V_{DS}$	30	V			
Gate-Source Voltage	$V_{GS}$	± 20	V			
	$T_A=25^{\circ}C$	T	6.4			
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	$\mathbf{I}_{\mathrm{D}}$	5.2	A		
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	± 30				
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.7	A		
D	$T_A=25^{\circ}C$	D	2.1	W		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	I <sub>L</sub> D	1.3	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
M · A · A · a	t <= 10 sec	D	62.5	°C/W			
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$ m R_{\theta JA}$	80	°C/W			

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Cymah al	Total Constitutions	Limits			T 1:4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static					•		
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
Zero Gate Voltage Brain Current	DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			30		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			A	
Drain-Source On-Resistance <sup>A</sup>	r	$r_{DS(on)}$ $V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$			35	mΩ	
Drain-Source On-Resistance	<sup>1</sup> DS(on)				45		
Forward Tranconductance <sup>A</sup>	$g_{\mathrm{fs}}$	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$		22		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		1			
Gate-Source Charge	$Q_{gs}$	$v_{DS} = 10 \text{ v}, v_{GS} = 4.3 \text{ v},$ $I_D = 2 \text{ A}$		0.4		nC	
Gate-Drain Charge	$Q_{\mathrm{gd}}$	$I_{\rm D} - 2 A$		0.7			
Turn-On Delay Time	t <sub>d(on)</sub>			2			
Rise Time	t <sub>r</sub>	$V_{DD} = 10 \text{ V}, R_L = 15 \Omega, I_D = 1 \text{ A},$		5		nS	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}$		10			
Fall-Time	t <sub>f</sub>			4			

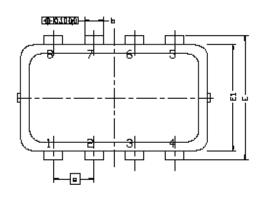
## Notes

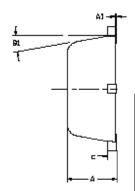
a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .

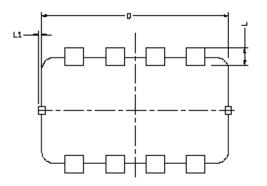
b. Guaranteed by design, not subject to production testing.

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## Package Information







DJM.	MILLIMETERS			INCHES			
	MEN		MAX	MIN	NOM	MAX	
Α	Q700	0.80	מספגם	0.0276	0.0315	0.0334	
Al	띦	-	0,05	0.000	-	0.002	
b	0.24	0.30	1.35	0.009	0.012	0.014	
C	91.0	0.152	1.25	0013	0,006	0,010	
D	3.00 BSC 0.318 BSC						
Ε	2.00 BSC 0.079 BSC						
E1	1,70 BSC   0,067 BSC						
6	¢	.65 BS	Ç	Ü	026 B:	;C	
L	0.20	0.275	0.400	0,000	0.011	0.0157	
Li	Ď		0.108	Ö		0.004	
<b>1</b> 1	Ü,	П	12*	Ů'	10"	12*	